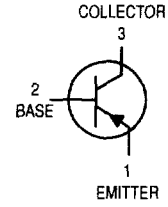
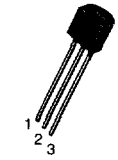
High Voltage Transistors
PNP Silicon

MPSA92*
MPSA93

*Motorola Preferred Device





CASE 29–04, STYLE 1
TO–92 (TO–226AA)

MAXIMUM RATINGS

Rating	Symbol	MPSA92	MPSA93	Unit
Collector–Emitter Voltage	V_{CEO}	–300	–200	Vdc
Collector–Base Voltage	V_{CBO}	–300	–200	Vdc
Emitter–Base Voltage	V_{EBO}	–5.0		Vdc
Collector Current — Continuous	I_C	–500		mAdc
Total Device Dissipation @ T_A = 25°C Derate above 25°C	P_D	625 5.0		mW mW/°C
Total Device Dissipation @ T_C = 25°C Derate above 25°C	P_D	1.5 12		Watts mW/°C
Operating and Storage Junction Temperature Range	T_J, T_{stg}	–55 to +150		°C

THERMAL CHARACTERISTICS

Characteristic	Symbol	Max	Unit
Thermal Resistance, Junction to Ambient	$R_{\theta JA}$	200	°C/W
Thermal Resistance, Junction to Case	$R_{\theta JC}$	83.3	°C/W

ELECTRICAL CHARACTERISTICS (T_A = 25°C unless otherwise noted)

Characteristic		Symbol	Min	Max	Unit
OFF CHARACTERISTICS					
Collector–Emitter Breakdown Voltage[1] (I_C = –1.0 mAdc, I_B = 0)	 MPSA92 MPSA93	$V_{(BR)CEO}$	 –300 –200	 — —	Vdc
Collector–Base Breakdown Voltage (I_C = –100 μAdc, I_E = 0)	 MPSA92 MPSA93	$V_{(BR)CBO}$	 –300 –200	 — —	Vdc
Emitter–Base Breakdown Voltage (I_E = –100 μAdc, I_C = 0)		$V_{(BR)EBO}$	–5.0	—	Vdc
Collector Cutoff Current (V_{CB} = –200 Vdc, I_E = 0) (V_{CB} = –160 Vdc, I_E = 0)	 MPSA92 MPSA93	I_{CBO}	 — —	 –0.25 –0.25	μAdc
Emitter Cutoff Current (V_{EB} = –3.0 Vdc, I_C = 0)		I_{EBO}	—	–0.1	μAdc

1. Pulse Test: Pulse Width ≤ 300 μs, Duty Cycle ≤ 2.0%.

Preferred devices are Motorola recommended choices for future use and best overall value.

ELECTRICAL CHARACTERISTICS (T_A = 25°C unless otherwise noted) (Continued)

Characteristic		Symbol	Min	Max	Unit
ON CHARACTERISTICS(1)					
DC Current Gain		h_{FE}			—
(I_C = −1.0 mAdc, V_{CE} = −10 Vdc)	Both Types		25	—	
(I_C = −10 mAdc, V_{CE} = −10 Vdc)	Both Types		40	—	
(I_C = −30 mAdc, V_{CE} = −10 Vdc)	MPSA92		25	—	
	MPSA93		25	—	
Collector–Emitter Saturation Voltage		$V_{CE(sat)}$			Vdc
(I_C = −20 mAdc, I_B = −2.0 mAdc)	MPSA92		—	−0.5	
	MPSA93		—	−0.4	
Base–Emitter Saturation Voltage (I_C = −20 mAdc, I_B = −2.0 mAdc)		$V_{BE(sat)}$	—	−0.9	Vdc
SMALL–SIGNAL CHARACTERISTICS					
Current–Gain — Bandwidth Product (I_C = −10 mAdc, V_{CE} = −20 Vdc, f = 100 MHz)		f_T	50	—	MHz
Collector–Base Capacitance		C_{cb}			pF
(V_{CB} = −20 Vdc, I_E = 0, f = 1.0 MHz)	MPSA92		—	6.0	
	MPSA93		—	8.0	

1. Pulse Test: Pulse Width ≤ 300 μs, Duty Cycle ≤ 2.0%.

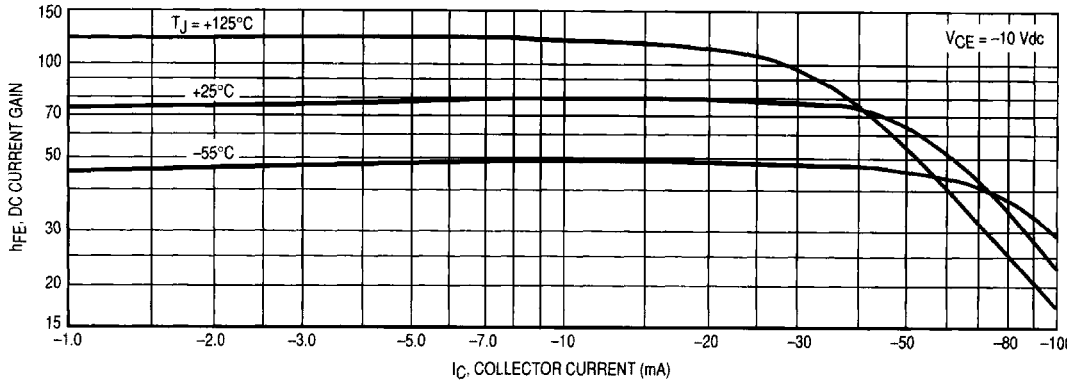


Figure 1. DC Current Gain

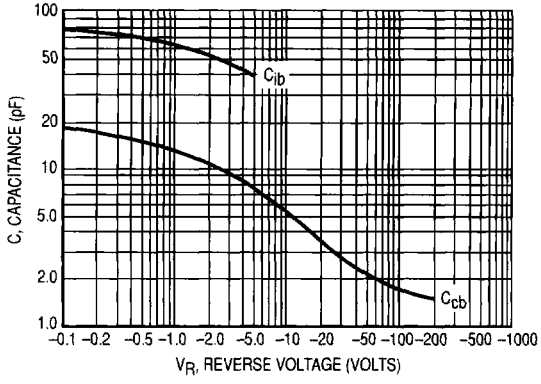


Figure 2. Capacitances

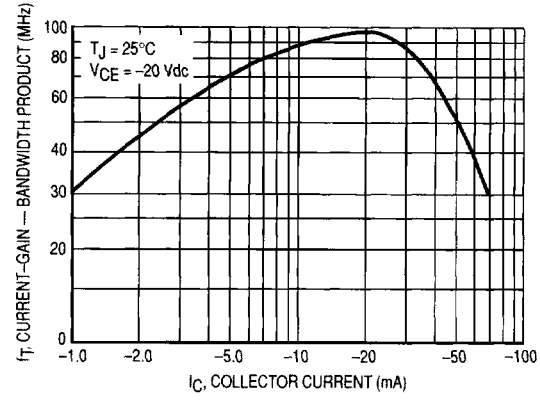


Figure 3. Current–Gain — Bandwidth Product

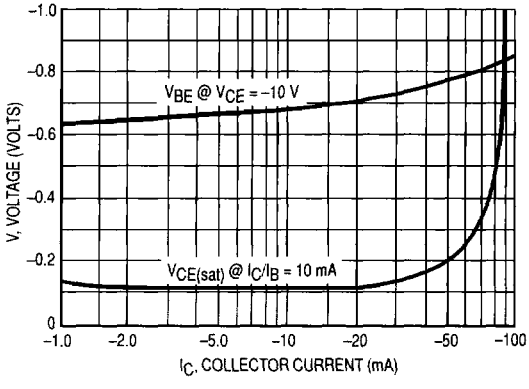


Figure 4. "On" Voltages

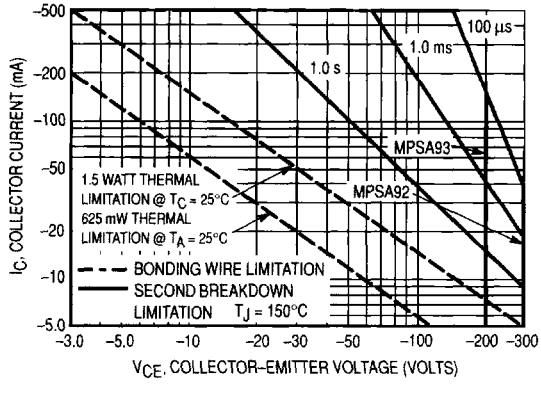


Figure 5. Active Region — Safe Operating Area